Product Summary

Device	BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_A = +25°C
Q1	30	0.4Ω @ V_{GS} = 10V	0.8A
		0.7Ω @ V_{GS} = 4.5V	0.62A
Q2	-30	0.9Ω @ V_{GS} = -10V	-0.55A
		1.7Ω @ V_{GS} = -4.5V	-0.4A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Description and Applications

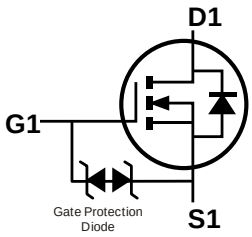
This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor Control
- Power Management Functions
- DC-DC Converters

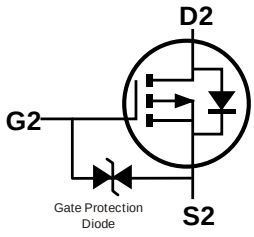
Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.027 grams (Approximate)

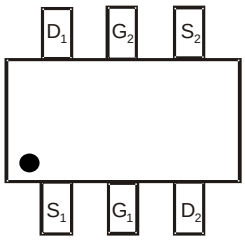
Top View



Q1 N-CHANNEL



Q2 P-CHANNEL



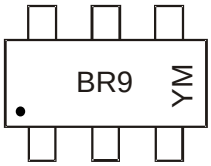
Top View
Pin out

Ordering Information (Note 4)

Part Number	Case	Packaging
DMC3401LDW-7	SOT363	3000/Tape & Reel
DMC3401LDW-13	SOT363	10000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



BR9 = Product Type Marking Code
YM = Date Code Marking
Y or $\overline{Y}$ or $\underline{Y}$= Year (ex: G = 2019)
M = Month (ex: 9 = September)

Date Code Key

Year	2018	2019	2020	2021	2022	2023	2024	2025
Code	F	G	H	I	J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value_Q1	Value_Q2	Unit
Drain-Source Voltage			V_{DSS}	30	-30	V
Gate-Source Voltage			V_{GSS}	±20	±20	V
Continuous Drain Current (Note 6) Q1: V_{GS} = 10V Q2: V_{GS} = -10V	Steady State	T_A = +25°C T_A = +70°C	I_D	0.8 0.6	-0.55 -0.44	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	0.4	-0.38	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	4	-2.4	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	0.29	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	433	°C/W
Total Power Dissipation (Note 6)		P_D	0.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	301	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics – N Channel – Q1 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	-	-	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	-	-	1.0	µA	V_{DS} = 30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	-	-	±10	µA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.8	1.2	1.6	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	-	0.2	0.4	Ω	V_{GS} = 10V, I_D = 0.59A
		-	0.3	0.7		V_{GS} = 4.5V, I_D = 0.2A
Diode Forward Voltage	V_{SD}	-	0.7	1.2	V	V_{GS} = 0V, I_S = 0.1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	-	50	-	pF	V_{DS} = 15V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	-	12	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	10	-	pF	
Gate Resistance	R_g	-	58	-	Ω	V_{DS} = V_{GS} = 0V, f = 1.0MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	-	0.5	-	nC	V_{DS} = 10V, I_D = 250mA
Total Gate Charge (V_{GS} = 10V)	Q_g	-	1.2	-	nC	
Gate-Source Charge	Q_{gs}	-	0.2	-	nC	
Gate-Drain Charge	Q_{gd}	-	0.1	-	nC	
Turn-On Delay Time	$t_{D(ON)}$	-	3.5	-	ns	V_{GS} = 10V, V_{DS} = 30V, I_D = 100mA, R_G = 25Ω
Turn-On Rise Time	t_R	-	3.3	-	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	-	16.8	-	ns	
Turn-Off Fall Time	t_F	-	13.8	-	ns	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

Electrical Characteristics – P Channel – Q2 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	-	-	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	-	-	-1	µA	V_{DS} = -24V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	-	-	±10	µA	V_{GS} = ±16V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	-1	-2.2	-2.6	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	-	0.5	0.9	Ω	V_{GS} = -10V, I_D = -0.42A
		-	0.78	1.7		V_{GS} = -4.5V, I_D = -0.2A
Diode Forward Voltage	V_{SD}	-	-0.8	-1.2	V	V_{GS} = 0V, I_S = -0.23A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	-	19	-	pF	V_{DS} = -15V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	-	16	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	3	-	pF	
Gate Resistance	R_g	-	4.4	-	kΩ	V_{DS} = V_{GS} = 0V, f = 1.0MHz
Total Gate Charge (V_{GS} = -4.5V)	Q_g	-	0.36	-	nC	V_{DS} = -10V, I_D = -0.24A
Total Gate Charge (V_{GS} = -10V)	Q_g	-	0.8	-	nC	
Gate-Source Charge	Q_{gs}	-	0.1	-	nC	
Gate-Drain Charge	Q_{gd}	-	0.1	-	nC	
Turn-On Delay Time	$t_{D(ON)}$	-	3.3	-	ns	V_{GS} = -10V, V_{DD} = -15V, I_D = -0.5A, R_G = 1Ω
Turn-On Rise Time	t_R	-	2.3	-	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	-	406	-	ns	
Turn-Off Fall Time	t_F	-	237	-	ns	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

Typical Characteristics - N-CHANNEL

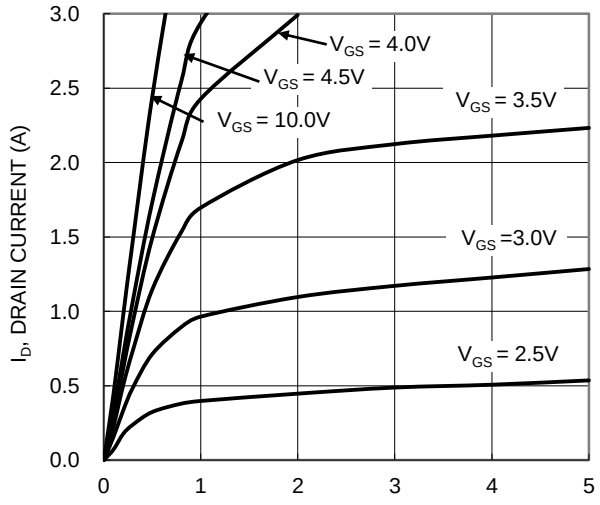


Figure 1.Typical Output Characteristic

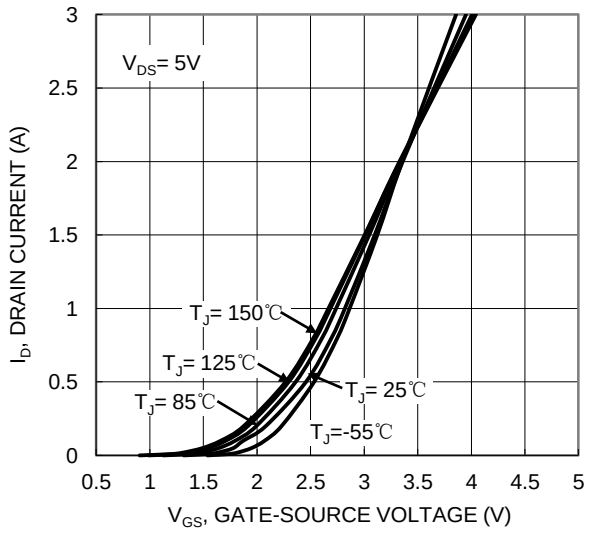


Figure 2. Typical Transfer Characteristic

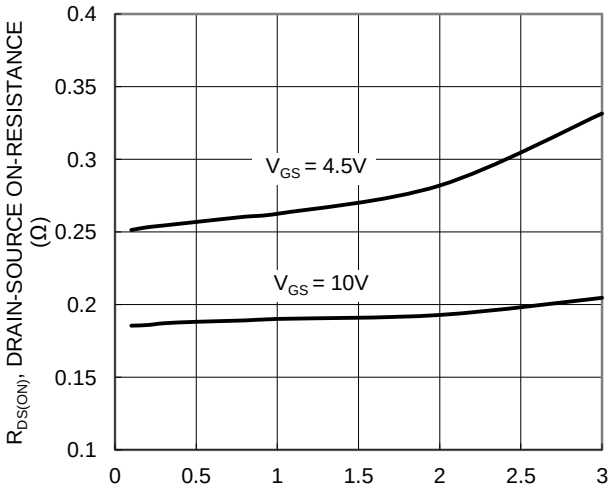


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

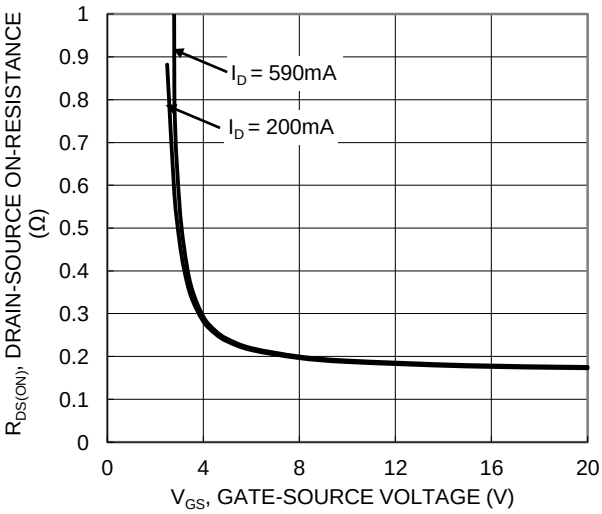


Figure 4. Typical Transfer Characteristic

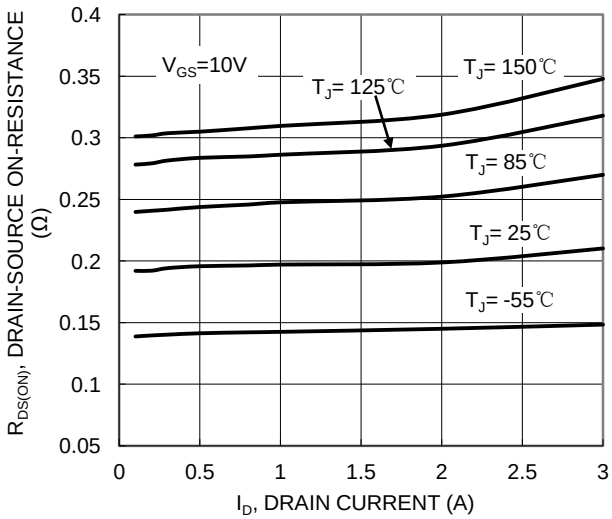


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

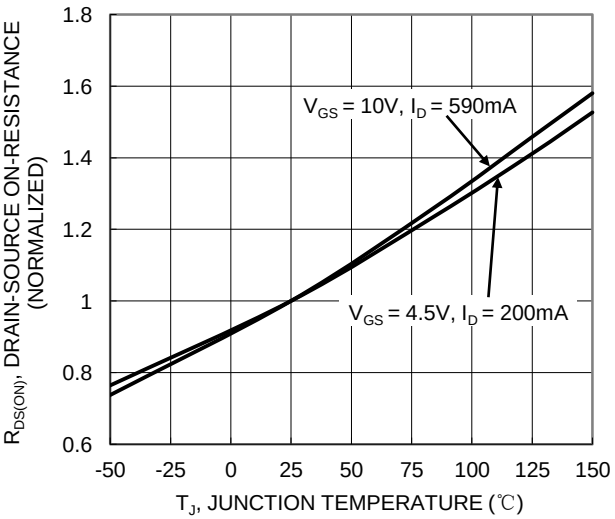


Figure 6. On-Resistance Variation with Temperature

Typical Characteristics - N-CHANNEL (Cont.)

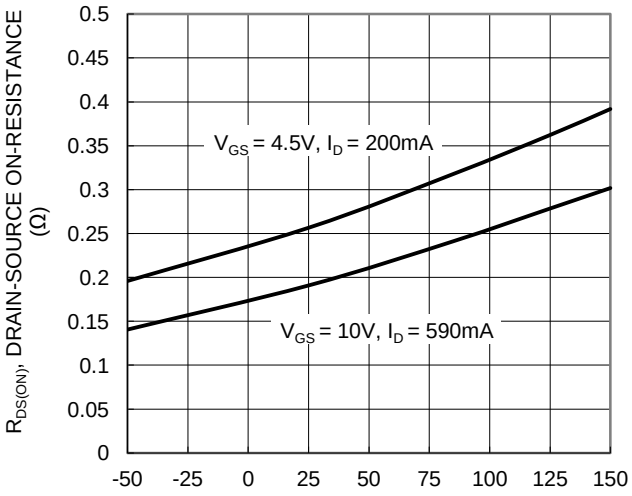


Figure 7. On-Resistance Variation with Temperature

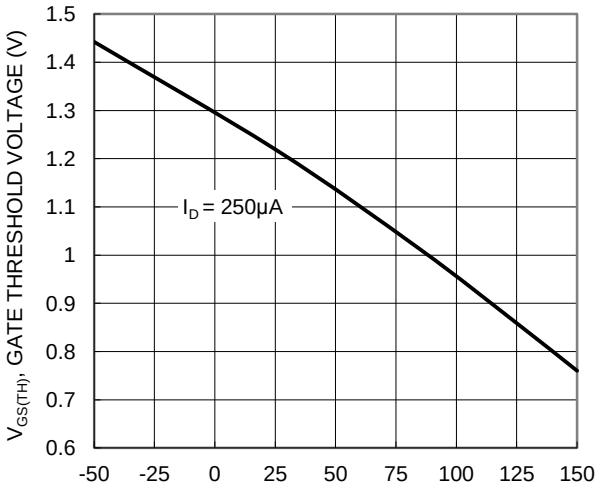


Figure 8. Gate Threshold Variation vs. JunctionTemperature

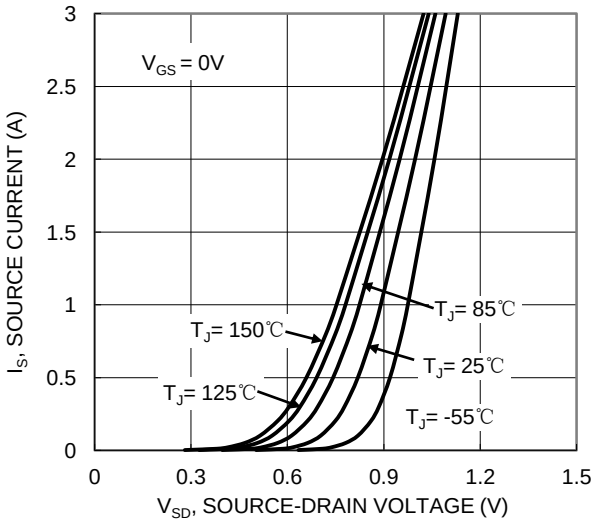


Figure 9. Diode Forward Voltage vs. Current

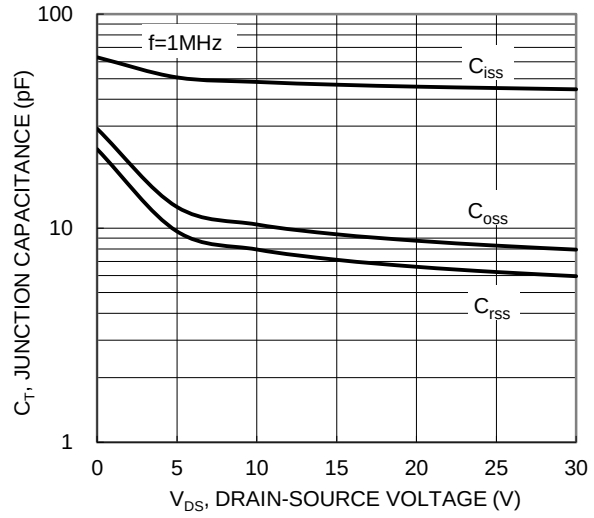


Figure 10. Typical Junction Capacitance

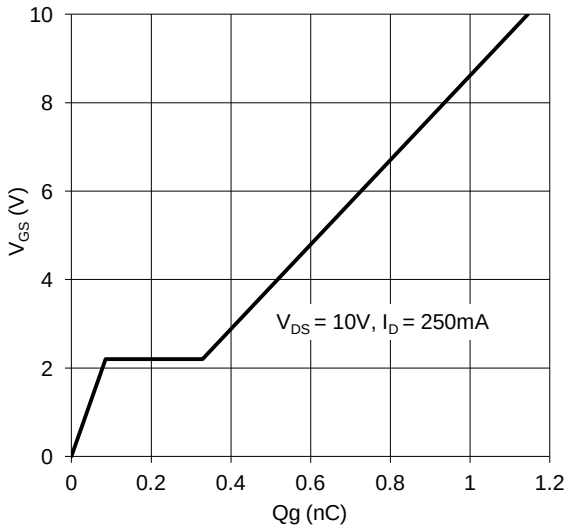


Figure 11. Gate Charge

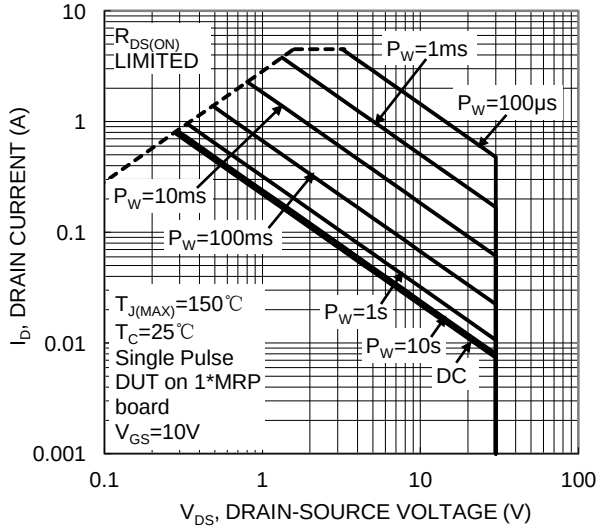


Figure 12. SOA, Safe Operation Area

Typical Characteristics - P-CHANNEL

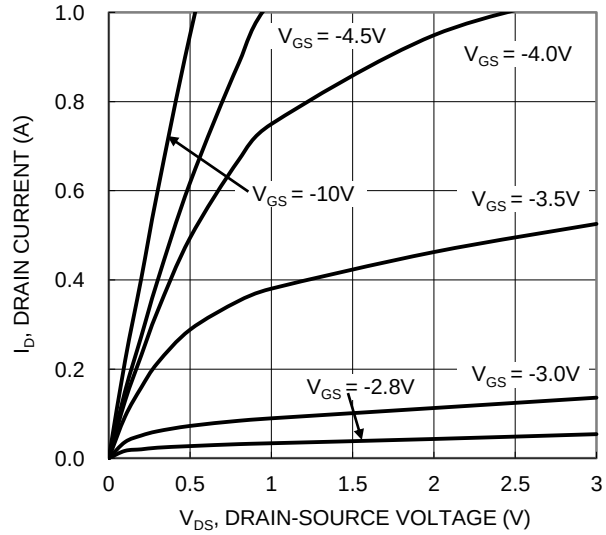


Figure 13. Typical Output Characteristic

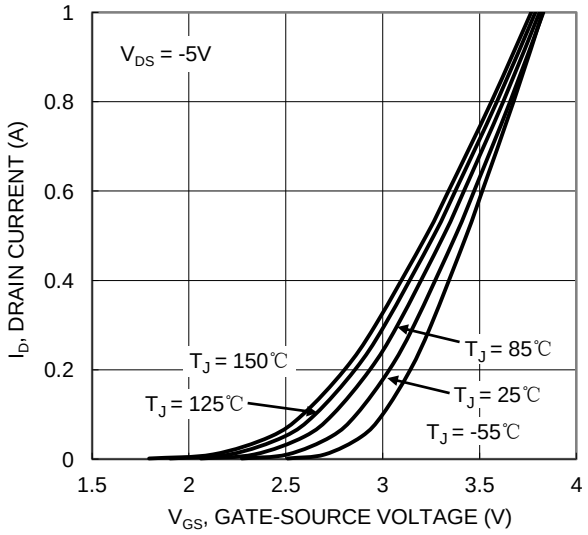


Figure 14. Typical Transfer Characteristic

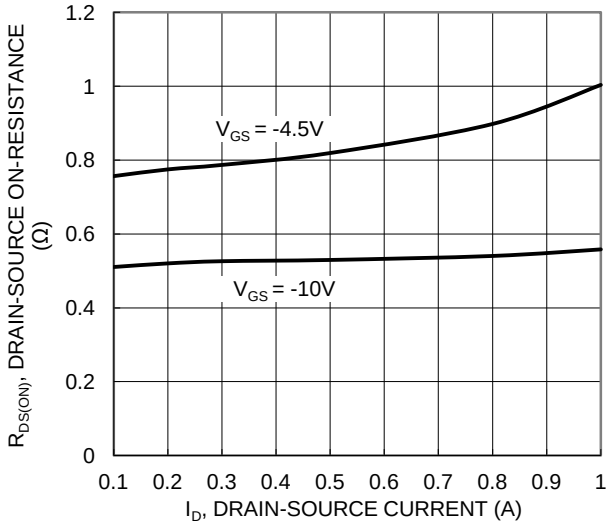


Figure 15. Typical On-Resistance vs. Drain Current and Gate Voltage

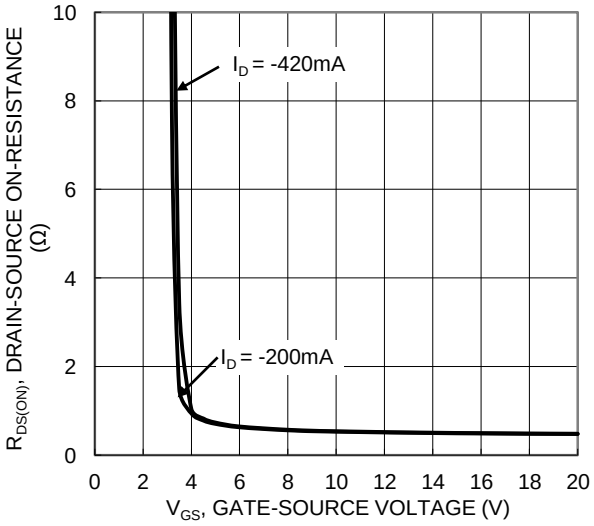


Figure 16. Typical Transfer Characteristic

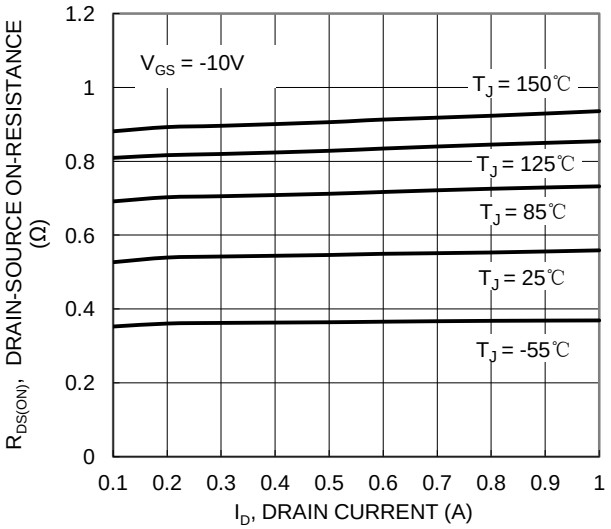


Figure 17. Typical On-Resistance vs. Drain Current and Junction Temperature

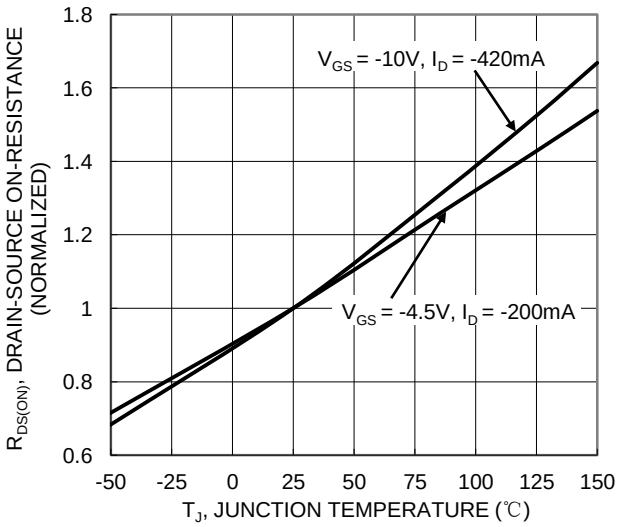


Figure 18. On-Resistance Variation with Junction Temperature

Typical Characteristics - P-CHANNEL (Cont.)

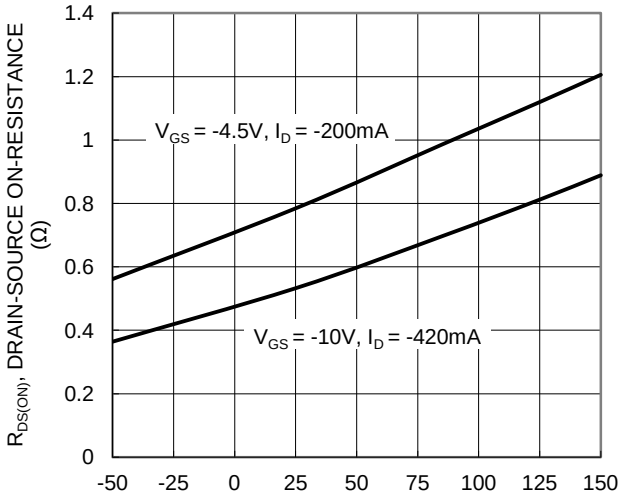


Figure 19. On-Resistance Variation with Junction Temperature

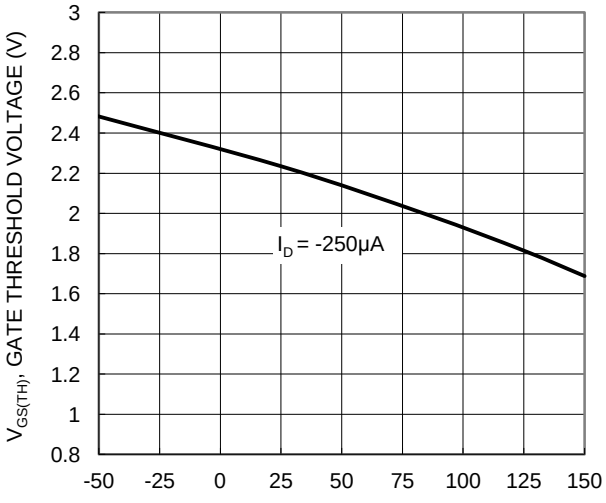


Figure 20. Gate Threshold Variation vs. Junction Temperature

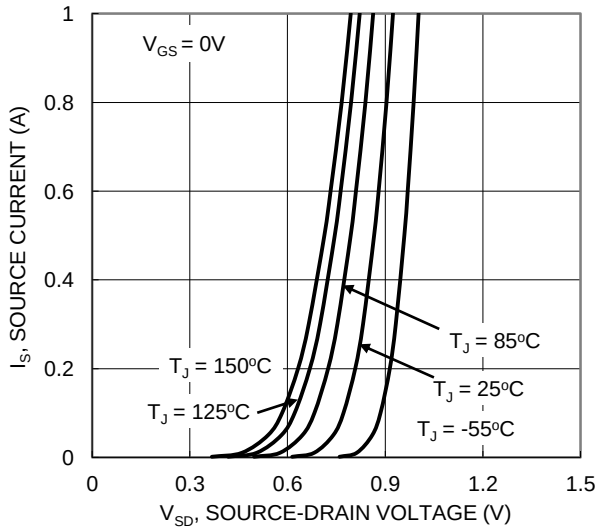


Figure 21. Diode Forward Voltage vs. Current

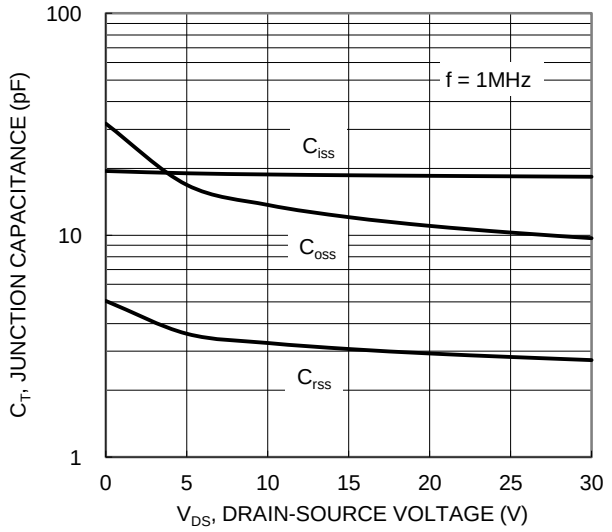


Figure 22. Typical Junction Capacitance

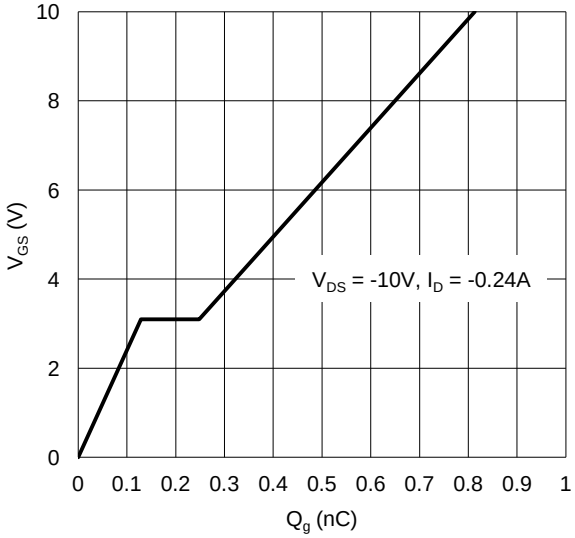


Figure 23. Gate Charge

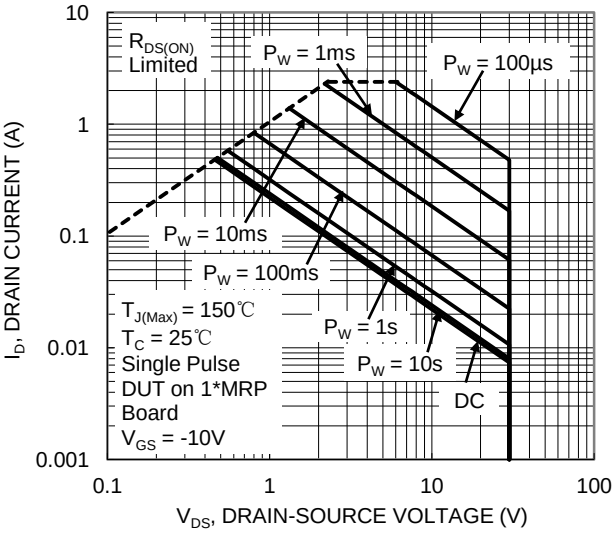


Figure 24. SOA, Safe Operation Area

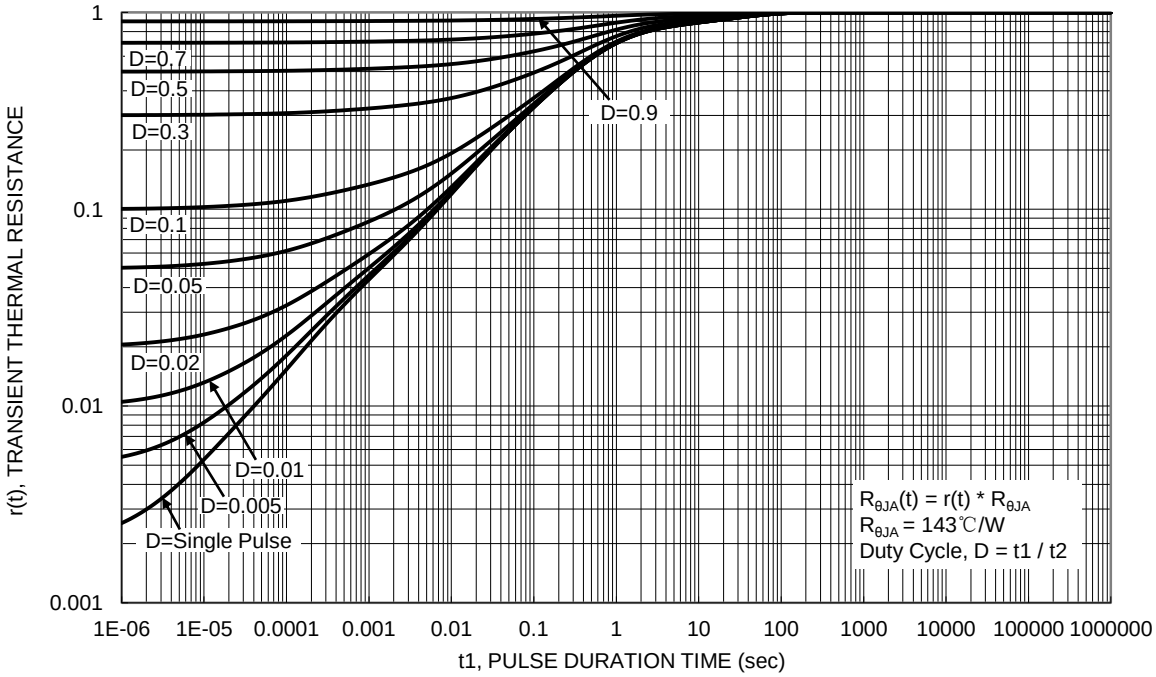
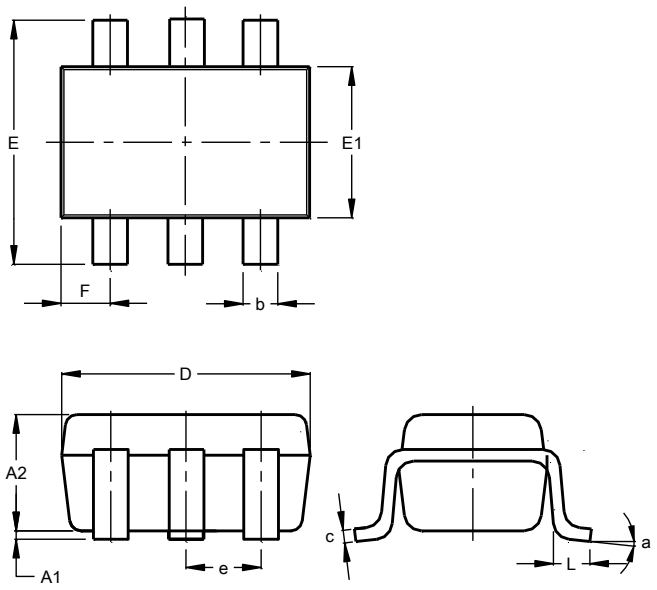


Figure 25. Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363

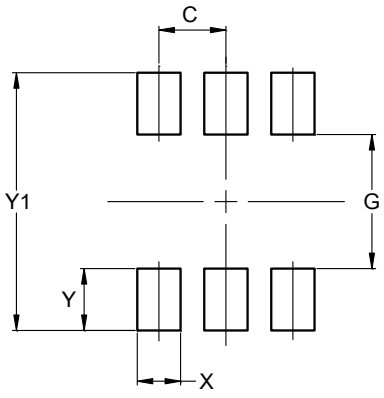


SOT363			
Dim	**Min**	**Max**	**Typ**
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500

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A. Life support devices or systems are devices or systems which:

1. are intended to implant into the body, or

2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

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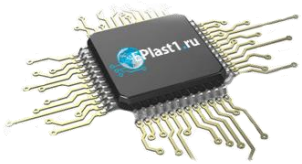
Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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